

28. (withdrawn) An integrated circuit having a field-plated resistor
the field-plated resistor comprising:

- a. a resistor body formed in a semiconductor substrate, the resistor body having first and second contact regions,
- b. a first insulating layer on the resistor body, the first insulating layer approximately coextensive with the resistor body and having a top surface and a bottom surface,
- c. a contact window in the first insulating layer and extending from the top surface of the first insulating layer through the first insulating layer to the resistor body,
- d. a field plate on the first insulating layer and approximately coextensive therewith and with the resistor body, the field plate having a top surface and a bottom surface, with a portion of the bottom surface extending through the contact window in the first insulating layer and into contact with the first contact region of the resistor,
- e. a second insulating layer, with a first portion of the second insulating layer at least substantially covering the field plate,
- f. an electrical contact extending through the first portion of the second insulating layer to the top surface of the field plate,
- g. an electrical contact to the second contact region of the resistor, and electrically insulated from the field plate, and

h. a plurality of metal conductors formed on the first portion of the second insulating layer.

29. (withdrawn) The integrated circuit of claim 28 wherein the field plate comprises polysilicon.

30. (withdrawn) The integrated circuit of claim 29 wherein the first and second insulating layers are SiO₂.

31. (canceled)

32. (withdrawn) The integrated circuit of claim 29 further comprising an insulative spacer formed around the field plate.

33. (withdrawn) The integrated circuit of claim 29 wherein the electrical contact to the top surface of the field plate comprises a barrier layer.

34. (withdrawn) The integrated circuit of claim 33 wherein the electrical contact to the second contact region of the resistor comprises a barrier layer.

35. (withdrawn) An integrated circuit having a field-plated resistor
the field-plated resistor comprising:

- a. a resistor body formed in a semiconductor substrate, the resistor body having first and second resistor contact regions,
- b. a first insulating layer on the resistor body, the first insulating layer approximately coextensive with the resistor body and having a top surface and a bottom surface,
- c. a contact window in the first insulating layer and extending from the top surface of the first insulating layer through the first insulating layer to the resistor body,
- d. a field plate on the first insulating layer and approximately coextensive therewith and with the resistor body, the field plate having a top surface and a bottom surface, with a portion of the bottom surface extending through the contact window in the first insulating layer and into contact with the first contact region of the resistor,
- e. a second insulating layer, with a first portion of the second insulating layer at least substantially covering the field plate and said second resistor contact region,
- f. a metal layer on said first portion of the second insulating layer, the metal layer comprising
 - i. an electrical contact to the top surface of the field plate,

- ii. an electrical contact to the second contact region of the resistor, and electrically insulated from the field plate, and
- iii. a plurality of metal conductors formed on the first portion of the second insulating layer.

36. (previously presented) A method for the manufacture of an integrated circuit having a field-plated resistor the field-plated resistor comprising:

- a. forming a resistor body in a semiconductor substrate, the resistor body having first and second contact regions,
- b. a first insulating layer on the resistor body, the first insulating layer approximately coextensive with the resistor body and having a top surface and a bottom surface,
- c. forming a contact window in the first insulating layer and extending from the top surface of the first insulating layer through the first insulating layer to the resistor body,
- d. forming a field plate on the first insulating layer and approximately coextensive therewith and with the resistor body, the field plate having a top surface and a bottom surface, with a portion of the bottom surface extending through the contact window in the first insulating layer and into contact with the first contact region of the resistor,

- e. depositing a second insulating layer, with a first portion of the second insulating layer at least substantially covering the field plate,
- f. depositing a metal layer, with a portion of the metal layer covering the first portion of the second insulating layer,
- g. patterning said portion of the metal layer to form
 - i. an electrical contact to the top surface of the field plate, and
 - ii. a plurality of metal conductors formed on the first portion of the second insulating layer.

37. (previously presented) The method of claim 36 wherein the field plate comprises polysilicon.

38. (previously presented) The method of claim 37 wherein the first and second insulating layers are SiO₂.

39. (previously presented) The method of claim 38 further including the step of forming an insulative spacer formed around the field plate.

40. (withdrawn) The method of claim 28 wherein the electrical contact to the top surface of the field plate overlies the portion of the bottom surface of the field plate that extends through the contact window in the

first insulating layer and into contact with the first contact region of the resistor.

41. (previously presented) The method of claim 36 wherein the electrical contact to the top surface of the field plate overlies the portion of the bottom surface of the field plate that extends through the contact window in the first insulating layer and into contact with the first contact region of the resistor.

42. (previously presented) The method of claim 36 wherein the said portion of the metal layer is additionally patterned to form an electrical contact to the second contact region of the resistor.